

## BDX33/A/B/C

### **Power Linear and Switching Applications**

- High Gain General Purpose
- Power Darlington TR
- Complement to BDX34/34A/34B/34C respectively



1.Base 2.Collector 3.Emitter

# **NPN Epitaxial Silicon Transistor**

## Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage		
	: BDX33	45	V
	: BDX33A	60	V
	: BDX33B	80	V
	: BDX33C	100	V
V <sub>CEO</sub>	Collector-Emitter Voltage		
	: BDX33	45	V
	: BDX33A	60	V
	: BDX33B	80	V
	: BDX33C	100	V
I <sub>C</sub>	Collector Current (DC)	10	А
СР	*Collector Current (Pulse)	15	А
l <sub>B</sub>	Base Current	0.25	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	70	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 65 ~ 150	°C

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Electrical	Characteristics	T <sub>C</sub> =25°C unless otherwise noted
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Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V <sub>CEO</sub> (sus)	*Collector-Emitter Sustaining Voltage : BDX33 : BDX33A : BDX33B : BDX33C	I <sub>C</sub> = 100mA I <sub>B</sub> = 0	45 60 80 100			V V V
V <sub>CER</sub> (sus)	* Collector-Emitter Sustaining Voltage : BDX33 : BDX33A : BDX33B : BDX33C	$I_{C} = 100 \text{mA}, I_{B} = 0$ $R_{BE} = 100 \Omega$	45 60 80 100			V V V
V <sub>CEV</sub> (sus)	* Collector-Emitter Sustaining Voltage : BDX33 : BDX33A : BDX33B : BDX33C	I <sub>C</sub> = 100mA, I <sub>B</sub> = 0 V <sub>BE</sub> = 1.5V	45 60 80 100			V V V
I <sub>CBO</sub>	Collector Cut-off Current : BDX33 : BDX33A : BDX33B : BDX33C	$V_{CB} = 45V, I_{E} = 0$ $V_{CB} = 60V, I_{E} = 0$ $V_{CB} = 80V, I_{E} = 0$ $V_{CB} = 100V, I_{E} = 0$			0.2 0.2 0.2 0.2	mA mA mA
I <sub>CEO</sub>	Collector Cut-off Current : BDX33 : BDX33A : BDX33B : BDX33C	V <sub>CE</sub> = 22V, I <sub>B</sub> = 0 V <sub>CE</sub> = 30V, I <sub>B</sub> = 0 V <sub>CE</sub> = 40V, I <sub>B</sub> = 0 V <sub>CE</sub> = 50V, I <sub>B</sub> = 0			0.5 0.5 0.5 0.5	mA mA mA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			5	mA
h <sub>FE</sub>	* DC Current Gain : BDX33/34 : BDX33B/33C	$V_{CE} = 3V, I_{C} = 4A$ $V_{CE} = 3V, I_{C} = 3A$	750 750			
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage : BDX33/33A : BDX33B/33C	$I_C = 4A, I_B = 8mA$ $I_C = 3A, I_B = 6mA$			2.5 2.5	V
V <sub>BE</sub> (on)	* Base-Emitter ON Voltage : BDX33/33A : BDX33B/33C	$V_{CE} = 3V, I_{C} = 4A$ $V_{CE} = 3V, I_{C} = 3A$			2.5 2.5	V V
V <sub>F</sub>	* Parallel Diode Forward Voltage	I <sub>F</sub> = 8A			4	V

<sup>\*</sup> Pulse Test: PW=300μs, duty Cycle =1.5% Pulse

# **Typical Characteristics**

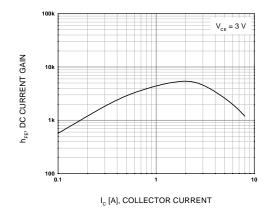


Figure 1. DC Current Gain

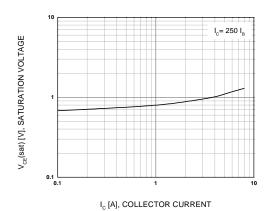


Figure 2. Collector-Emitter Saturation Voltage

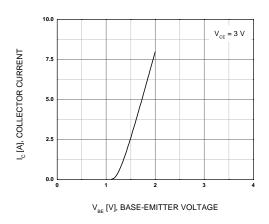


Figure 3. Base-Emitter On Voltage

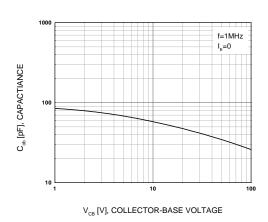


Figure 4. Output Capacitance

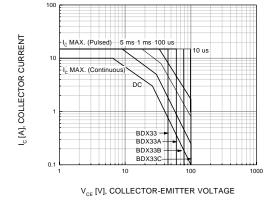


Figure 5. Safe Operating Area

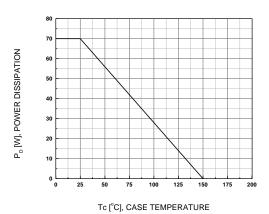
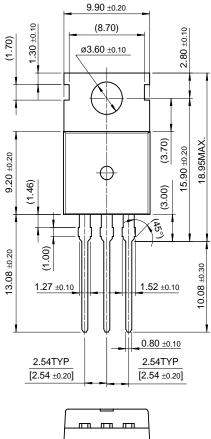


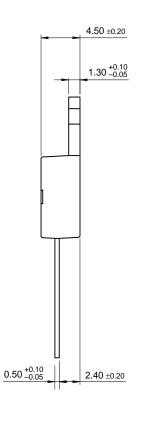
Figure 6. Power Derating

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# **Package Demensions**

# TO-220





10.00 ±0.20

Dimensions in Millimeters

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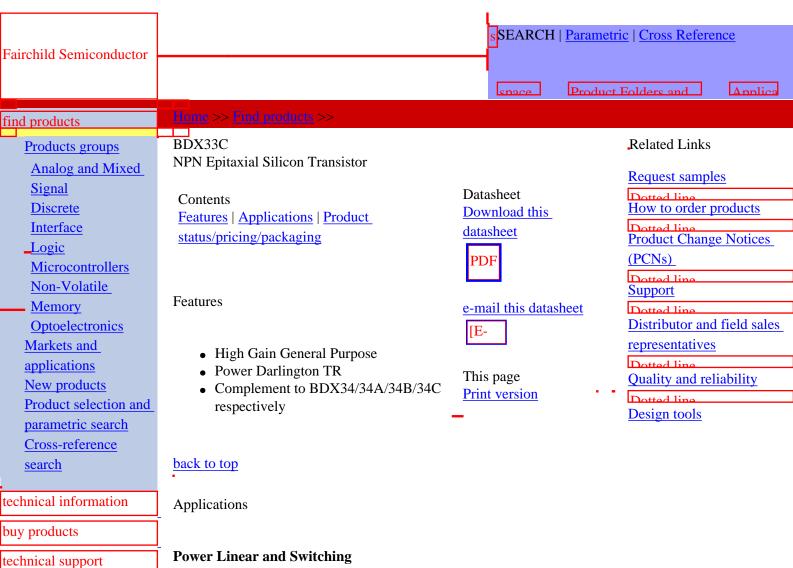
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back to top

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### Product status/pricing/packaging

Product	Product status	Pricing*	Package type	Leads	Packing method
BDX33C	Full Production	\$0.468	TO-220	3	BULK
BDX33CTU	Full Production	\$0.468	TO-220	3	RAIL

<sup>\* 1,000</sup> piece Budgetary Pricing

### back to top

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